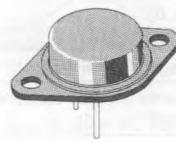


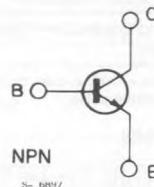
POWER LINEAR AND SWITCHING APPLICATIONS

DESCRIPTION

The 2N3055 is a silicon epitaxial-base NPN transistor in Jedecl TO-3 metal case. It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers.



TO-3

INTERNAL SCHEMATIC DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base Voltage ($I_E = 0$)	100	V
V_{CER}	Collector-emitter Voltage ($R_{BE} = 100 \Omega$)	70	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	60	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	15	A
I_B	Base Current	7	A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25^\circ\text{C}$	115	W
T_{stg}	Storage Temperature	-65 to 200	°C
T_J	Junction Temperature	200	°C

THERMAL DATA

$R_{th(j-case)}$	Thermal Resistance Junction-case	Max	1.5	°C/W
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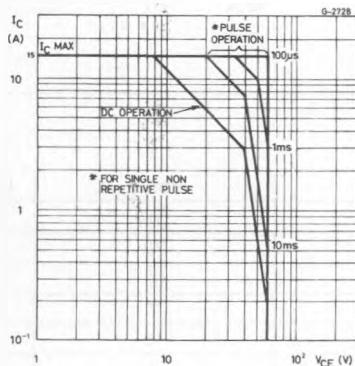
ELECTRICAL CHARACTERISTICS ($T_{case} = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
I_{CEV}	Collector Cutoff Current ($V_{BE} = -1.5\text{V}$)	$V_{CE} = 100\text{V}$				1	mA
		$V_{CE} = 100\text{V}$	$T_{case} = 150^\circ\text{C}$			5	mA
I_{CEO}	Collector Cutoff Current ($I_B = 0$)	$V_{CE} = 30\text{V}$				0.7	mA
I_{EBO}	Emitter Cutoff Current ($I_C = 0$)	$V_{EB} = 7\text{V}$				5	mA
$V_{CER(sus)}^*$	Collector-emitter Sustaining Voltage ($R_{BE} = 100\Omega$)	$I_C = 200\text{mA}$		70			V
$V_{CEO(sus)}^*$	Collector-emitter Sustaining Voltage ($I_B = 0$)	$I_C = 200\text{mA}$		60			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 4\text{A}$ $I_C = 10\text{A}$	$I_B = 400\text{mA}$ $I_B = 3.3\text{A}$			1 3	V
V_{BE}^*	Base-emitter Voltage	$I_C = 4\text{A}$	$V_{CE} = 4\text{V}$			1.5	V
h_{FE}^*	DC Current Gain						
	Group 4	$I_C = 0.5\text{A}$	$V_{CE} = 4\text{V}$	20		50	
	Group 5	$I_C = 0.5\text{A}$	$V_{CE} = 4\text{V}$	35		75	
	Group 6	$I_C = 0.5\text{A}$	$V_{CE} = 4\text{V}$	60		145	
	Group 7	$I_C = 0.5\text{A}$ $I_C = 4\text{A}$ $I_C = 10\text{A}$	$V_{CE} = 4\text{V}$ $V_{CE} = 4\text{V}$ $V_{CE} = 4\text{V}$	120 20 5		250 70	
h_{FE1}/h_{FE2}^*	Matched Pair	$I_C = 0.5\text{A}$	$V_{CE} = 4\text{V}$			1.6	
f_T	Transistion Frequency	$I_C = 1\text{A}$	$V_{CE} = 4\text{V}$	2.5			MHz
$I_{s/b}^*$	Second Breakdown Collector Current	$V_{CE} = 40\text{V}$		2.87			A

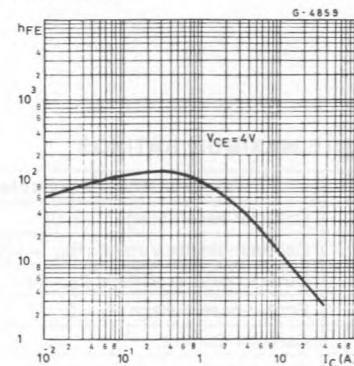
* Pulsed : pulse duration = 300μs, duty cycle = 1.5%.

** Pulsed : 1s, non repetitive pulse.

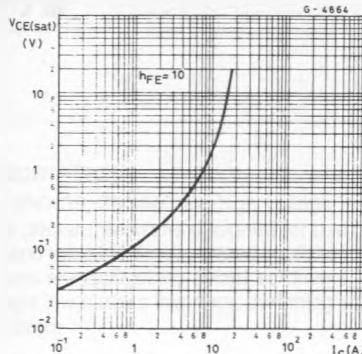
Safe Operating Areas.



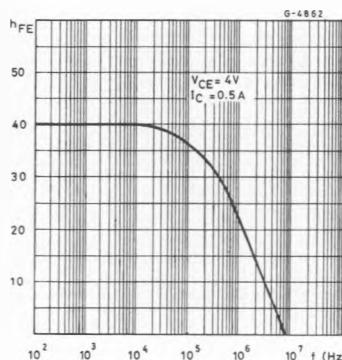
DC Current Gain.



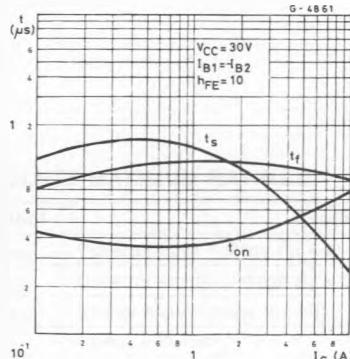
Collector-emitter Saturation Voltage.



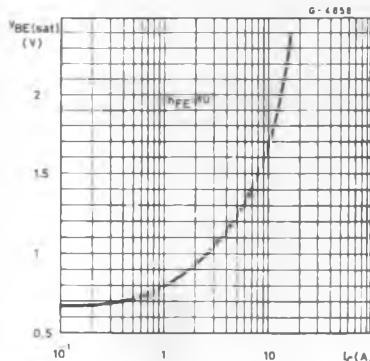
Small Signal Current Gain.



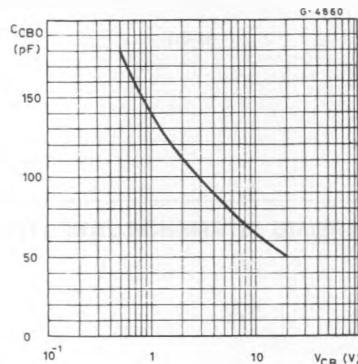
Saturated Switching Characteristics.



Base-emitter Saturation Voltage.



Collector-base Capacitance.



Power Rating Chart.

